



## Si4936CDY vs. Si4936BDY

**Description:** Dual P-Channel, 30-V (D-S) MOSFET

**Package:** SO-8

**Pin Out:** Identical

**Part Number Replacements:** Si4936CDY-T1-GE3 replaces Si4936BDY-T1-GE3  
Si4936CDY-T1-GE3 replaces Si4936BDY-T1-E3

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted					
PARAMETER	SYMBOL	Si4936CDY	Si4936BDY	UNIT	
Drain-Source Voltage	$V_{DS}$	30	30	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$		
Continuous Drain Current	$I_D$	$T_A = 25\text{ }^\circ\text{C}$	5.0	5.9	A
		$T_A = 70\text{ }^\circ\text{C}$	4.0	4.7	
Pulsed Drain Current	$I_{DM}$	20	30		
Continuous Source Current (MOSFET Diode Conduction)	$I_S$	1.4	1.7		
Power Dissipation	$P_D$	$T_A = 25\text{ }^\circ\text{C}$	1.7	2.0	W
		$T_A = 70\text{ }^\circ\text{C}$	1.1	1.3	
Operating Junction and Storage Temperature Range	$T_J$ and $T_{stg}$	- 55 to 150	- 55 to 150	$^\circ\text{C}$	
Maximum Junction-to-Ambient	$R_{thJA}$	75	62.5	$^\circ\text{C/W}$	

<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted								
PARAMETER	SYMBOL	Si4936CDY			Si4936BDY			UNIT
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
<b>Static</b>								
Gate-Threshold Voltage	$V_{GS(th)}$	1.2		3.0	1.5		3.0	V
Gate-Body Leakage	$I_{GSS}$			$\pm 100$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$			1			1	$\mu\text{A}$
On-State Drain Current	$V_{GS} = 10\text{ V}$ $I_{D(on)}$	15			30			A
Drain-Source On-Resistance	$V_{GS} = 10\text{ V}$ $R_{DS(on)}$		0.033	0.040		0.029	0.035	$\Omega$
	$V_{GS} = 4.5\text{ V}$		0.041	0.050		0.042	0.051	
Forward Transconductance	$g_{fs}$		15			12		S
Diode Forward Voltage	$V_{SD}$		0.8	1.2		0.8	1.2	V
<b>Dynamic</b>								
Total Gate Charge	$V_{GS} = 10\text{ V}$ $Q_g$		6	9		9.1	15	nC
	$V_{GS} = 4.5\text{ V}$		2.8	4.2		4.5	7	
Gate-Source Charge	$Q_{gs}$		1.1			1.8		
Gate-Drain Charge	$Q_{gd}$		0.8			1.7		
Gate Resistance	$R_g$	0.6	2.8	5.6		3		$\Omega$
<b>Switching</b>								
Turn-On-Time	$t_{d(on)}$		4	8		5	10	ns
	$t_r$		9	18		25	40	
Turn-Off-Time	$t_{d(off)}$		11	20		12	20	
	$t_f$		8	15		10	15	
Source-Drain Reverse Recovery Time	$t_{rr}$		11	20		20	40	

**Note**

NS denotes not specified in original specification

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.